

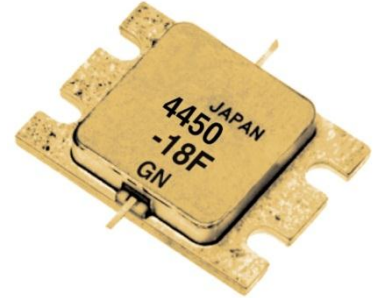
FEATURES

- High Output Power: $P_{1dB} = 43.0\text{dBm}$ (Typ.)
- High Gain: $G_{1dB} = 9.5\text{dB}$ (Typ.)
- High PAE: $\eta_{add} = 36\%$ (Typ.)
- Low IM3 = $-46\text{dBc}@P_o = 32.0\text{dBm}$
- Broad Band: 4.4 to 5.0 GHz
- Impedance Matched $Z_{in}/Z_{out} = 50\text{ohm}$
- Hermetically Sealed Package

DESCRIPTION

The FLM4450-18F is a power GaAs FET that is internally matched for standard communication bands to provide optimum power and gain in a 50 ohm system.

SEDI's stringent Quality Assurance Program assures the highest reliability and consistent performance.



ABSOLUTE MAXIMUM RATING (Ambient Temperature $T_a=25\text{deg.C}$)

Item	Symbol	Condition	Rating	Unit
Drain-Source Voltage	V_{DS}		15	V
Gate-Source Voltage	V_{GS}		-5	V
Total Power Dissipation	P_T	$T_c = 25\text{deg.C}$	83.3	W
Storage Temperature	T_{stg}		-65 to +175	deg.C
Channel Temperature	T_{ch}		175	deg.C

SEDI recommends the following conditions for the reliable operation of GaAs FETs:

1. The drain-source operating voltage (V_{DS}) should not exceed 10 volts.
2. The forward and reverse gate currents should not exceed 26.0 and -11.6 mA respectively with gate resistance of 25ohm.

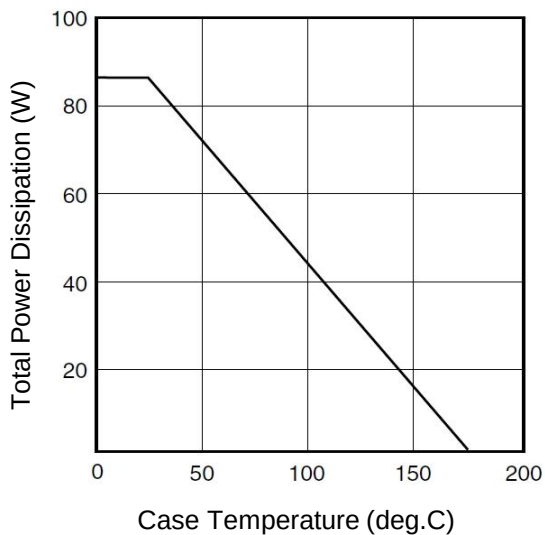
ELECTRICAL CHARACTERISTICS (Ambient Temperature $T_a=25\text{deg.C}$)

Item	Symbol	Test Conditions	Limit			Unit
			Min.	Typ.	Max.	
Saturated Drain Current	I_{DSS}	$V_{DS}=5V, V_{GS}=0V$	-	9.0	13.5	A
Transconductance	g_m	$V_{DS}=5V, I_{DS}=4800\text{mA}$	-	4000	-	mS
Pinch-off Voltage	V_p	$V_{DS}=5V, I_{DS}=480\text{mA}$	-1.0	-2.0	-3.5	V
Gate Source Breakdown Voltage	V_{GSO}	$I_{GS}=-480\text{uA}$	-5.0	-	-	V
Output Power at 1dB G.C.P.	P_{1dB}	$V_{DS}=10V,$	42.0	43.0	-	dBm
Power Gain at 1dB G.C.P.	G_{1dB}	$I_{DS}=0.55 I_{DSS}$ (Typ.),	8.5	9.5	-	dB
Drain Current	I_{dsr}	$f=4.4$ to 5.0 GHz,	-	4800	6000	mA
Power-added Efficiency	η_{add}	$Z_S=Z_L=50\text{ohm}$	-	36	-	%
Gain Flatness	ΔG		-	-	+/-0.6	dB
3rd Order Intermodulation Distortion	IM_3	$f = 5.0$ GHz, $\Delta f = 10$ MHz 2-Tone Test $P_{out} = 32.0\text{dBm}$ S.C.L.	-44	-46	-	dBc
Thermal Resistance	R_{th}	Channel to Case	-	1.6	1.8	deg.C/W
Channel Temperature Rise	ΔT_{ch}	$10V \times I_{dsr} \times R_{th}$	-	-	80	deg.C

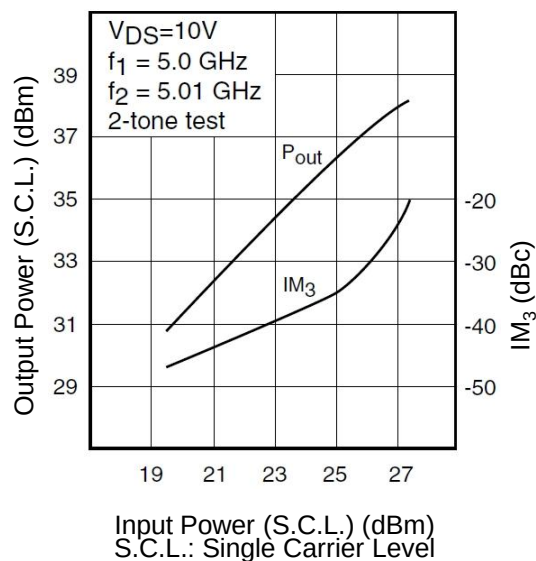
G.C.P.: Gain Compression Point, S.C.L.: Single Carrier Level

CASE STYLE	IK	
ESD	Class 3A	4000V to 8000V
Note : Based on EIAJ ED-4701 C-111A (C=100pF, R=1.5kohm)		
RoHS Compliance	Yes	

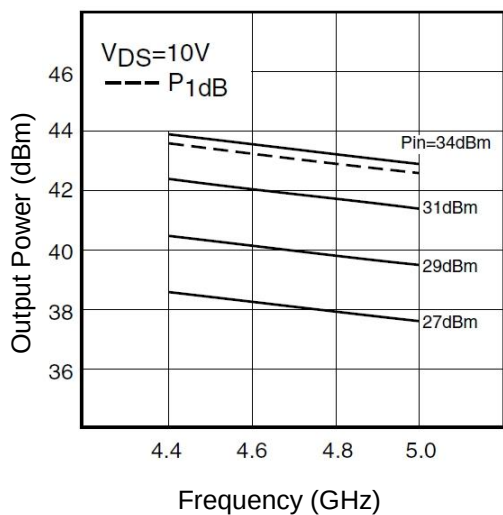
POWER DERATING CURVE



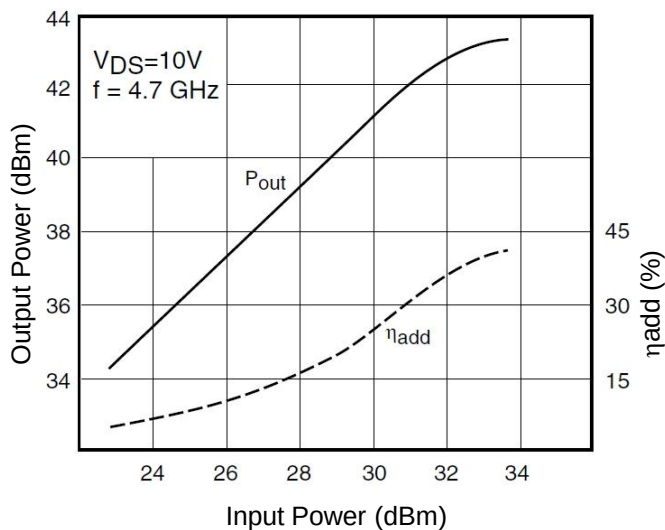
OUTPUT POWER & IM₃ vs. INPUT POWER

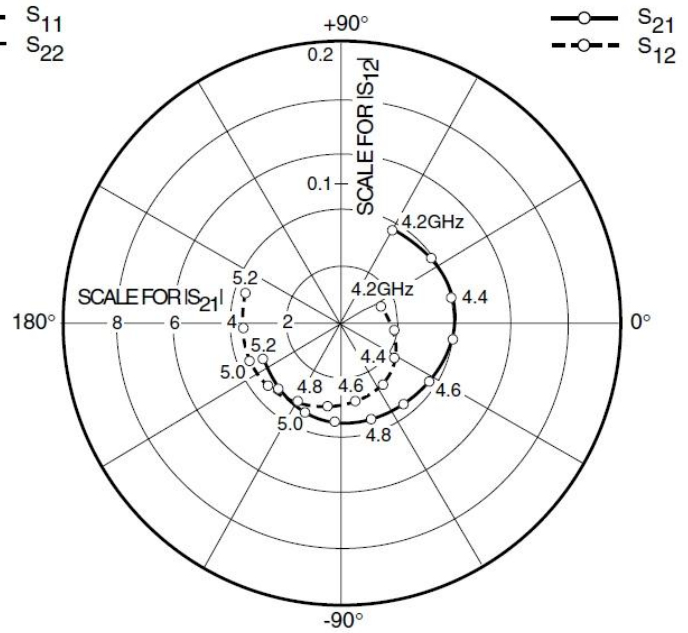
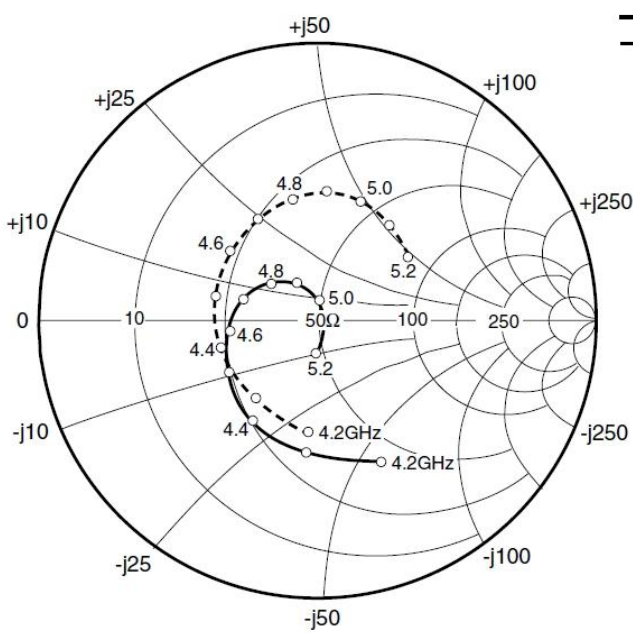


OUTPUT POWER vs. FREQUENCY



OUTPUT POWER vs. INPUT POWER



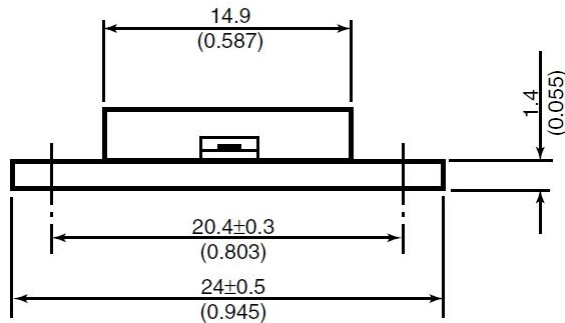
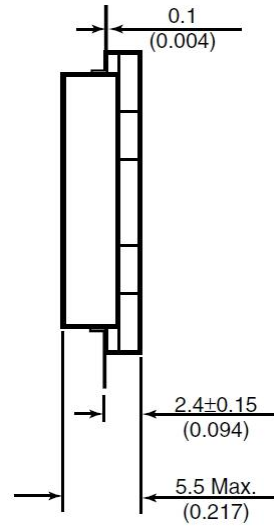
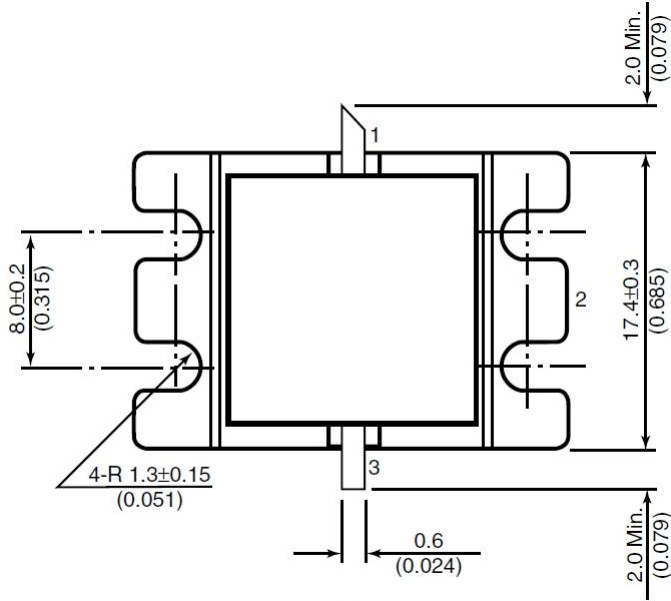


S-PARAMETERS

$V_{DS} = 10V$, $I_{DS} = 4800mA$

FREQUENCY (MHz)	S11		S21		S12		S22	
	MAG	ANG	MAG	ANG	MAG	ANG	MAG	ANG
4200	0.554	-65.9	3.802	59.9	0.030	22.4	0.404	-94.6
4300	0.481	-95.2	3.981	35.7	0.037	-6.9	0.357	-128.7
4400	0.426	-123.2	4.027	11.7	0.044	-32.7	0.355	-163.4
4500	0.374	-150.2	3.981	-11.1	0.052	-56.7	0.377	167.0
4600	0.324	-173.6	3.802	-32.6	0.056	-80.6	0.401	142.1
4700	0.277	164.3	3.717	-53.1	0.060	-101.1	0.423	120.5
4800	0.217	142.9	3.589	-73.0	0.064	-119.3	0.448	101.9
4900	0.157	120.8	3.508	-92.8	0.068	-140.0	0.464	85.8
5000	0.073	86.9	3.388	-113.1	0.072	-158.1	0.460	70.4
5100	0.033	-33.1	3.273	-133.9	0.070	-178.2	0.435	53.7
5200	0.119	-93.6	3.090	-154.9	0.072	162.9	0.400	36.0

Case Style "IK"
Metal-Ceramic Hermetic Package



1. Gate
2. Source (Flange)
3. Drain

Unit: mm(inches)



FLM4450-18F

C-Band Internally Matched FET

For further information please contact:

<http://global-sei.com/Electro-optic/about/office.html>

CAUTION

This product contains **gallium arsenide (GaAs)** which can be hazardous to the human body and the environment. For safety, observe the following procedures:

- Do not put these products into the mouth.
- Do not alter the form of this product into a gas, powder, or liquid through burning, crushing, or chemical processing as these by-products are dangerous to the human body if inhaled, ingested, or swallowed.
- Observe government laws and company regulations when discarding this product. This product must be discarded in accordance with methods specified by applicable hazardous waste procedures.